Capacitance Bridge for Characterizing 2D Materials

Gustavo Acosta University of California, Riverside Mentor: David Cobden

Outline

- Motivation
- Process of making 2D materials and nanodevices
- Design of Capacitance Bridge
- Expected Results and Future Work

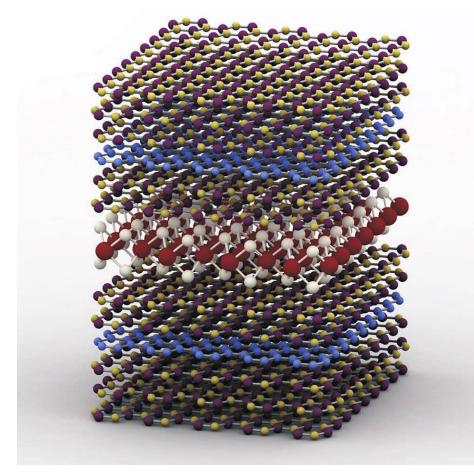
Van der Waals Structure

- Van der Waals materials are materials that consist of single plane of atoms
- Van der Waals Structures are structures made of layers of these materials that are held together by weak interactions between the layers
- Interesting because they have exotic properties that differ from their 3D counterparts

Light-emitting diodes by band-structure engineering in van der Waals heterostructures

F. Withers, O. Del Pozo-Zamudio, A. Mishchenko, A. P. Rooney, A. Gholinia, K. Watanabe, T. Taniguchi, S. J. Haigh, A. K. Geim, A. I. Tartakovskii & K. S. Novoselov 🖼

Nature Materials 14, 301–306 (2015) \mid Download Citation 🛓



Motivation

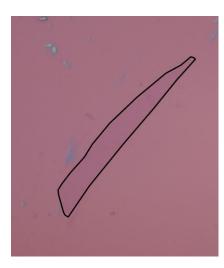
- Characterization of 2D materials is important to understanding and applications
- High Resolution Capacitance Bridge design can help to find the capacitance of these 2D materials
- Capacitance measurements are directly related to the density of states
- Use graphene as a general material
- If effective will be used to characterize more exotic materials such as WTe₂(tungsten ditelleride)

Materials Used

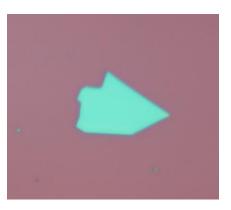


Graphite

- Thickness:11.2 nm
- Size: 35 microns
- Top of Structure



Hexagonal Boron Nitride



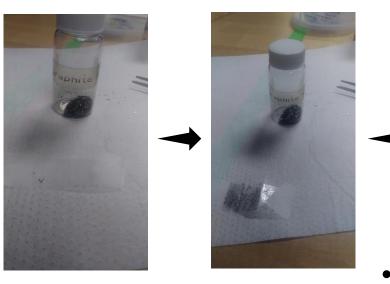
Graphene

- Thickness: 0.3 nm
- Length: 60 microns
- Bottom of Structure

h-BN

- Thickness:50 nm
- Length: 24 microns
- Middle of Structure

Method for Obtaining Materials



 Spread graphite crystals onto scotch tape for Exfoliation Exfoliate Crystals • Heat to 100°C onto plasma cleaned SiO₂ chips

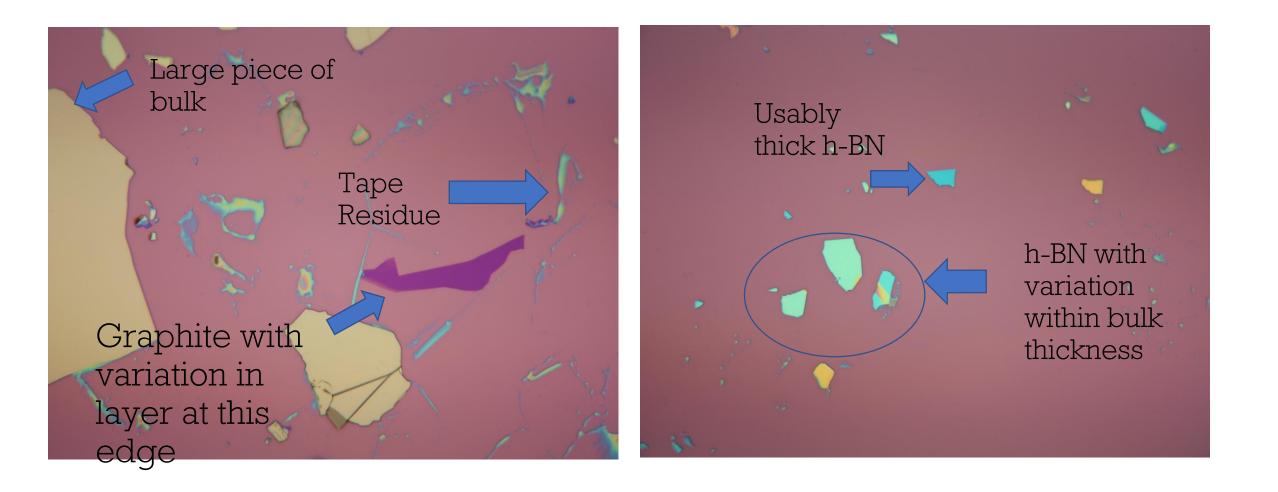




 Cool to Room Temperature and peel tape

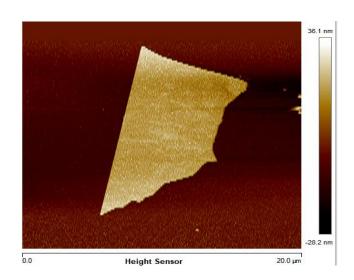
• Stick and Tear

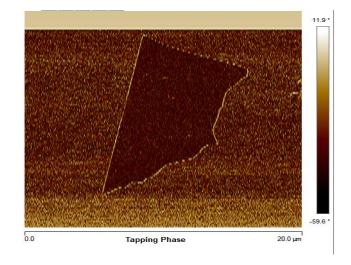
Searching for Materials



Characterizing Components





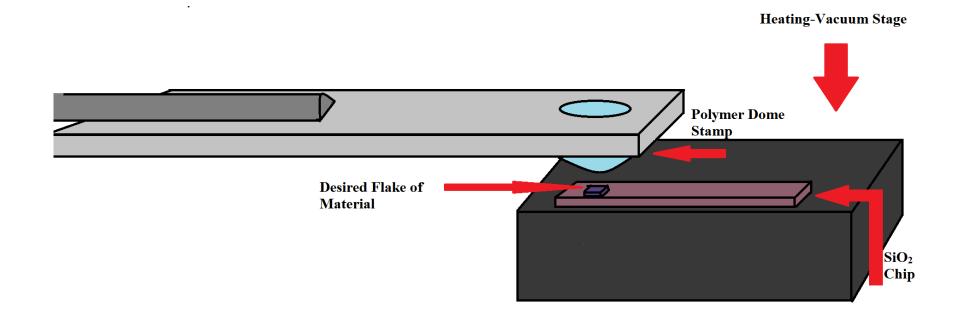


Optical Image

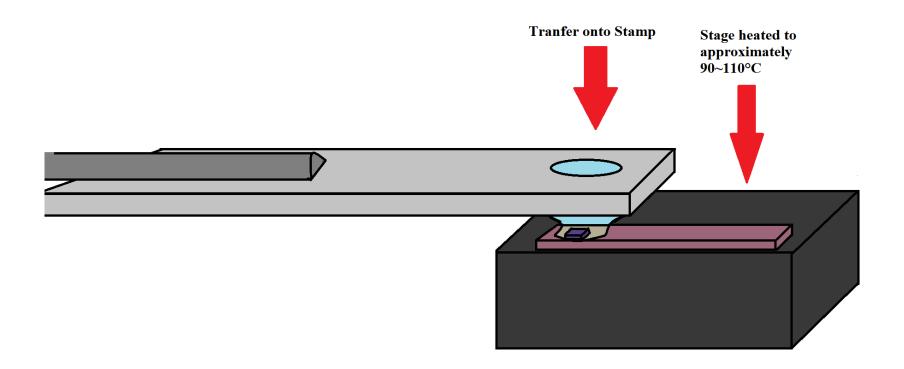
Thickness

Cleanliness

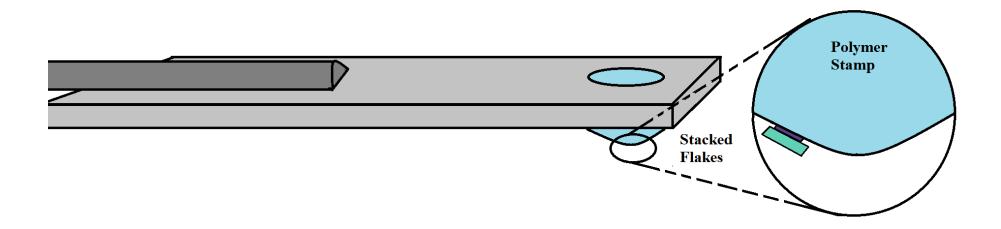
Position Stamp



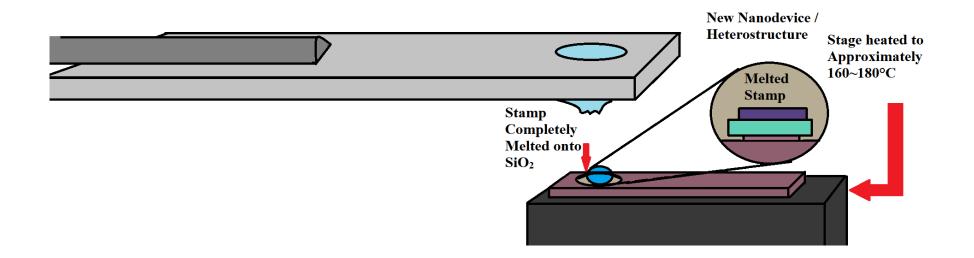
Pick-up material



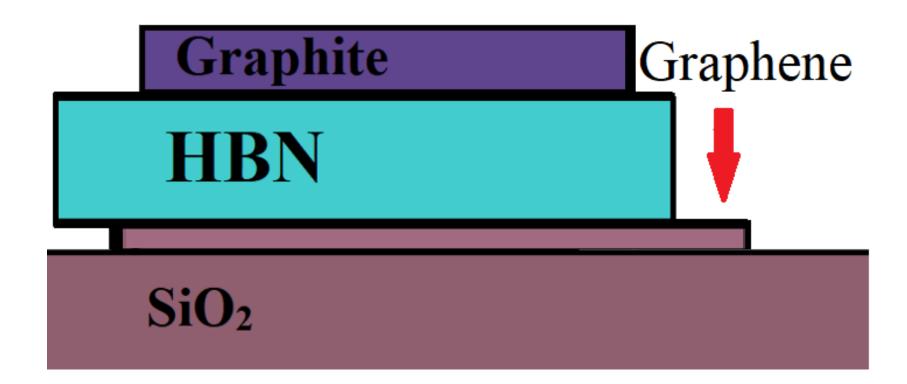
Desired Structure on Stamp



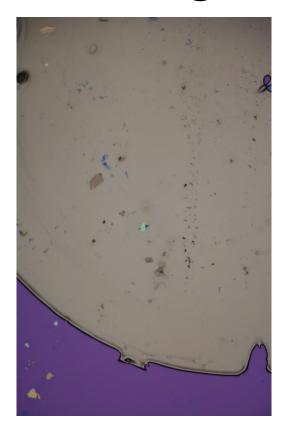
Melt Stamp onto Bottom Flake



Structure of Device

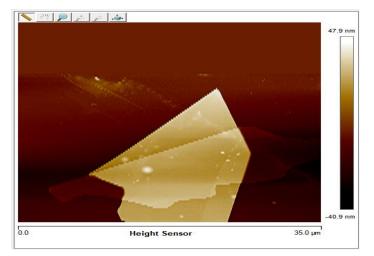


Design of the Structure



After cleaning in chloroform, and isopropanol, then annealing in furnace

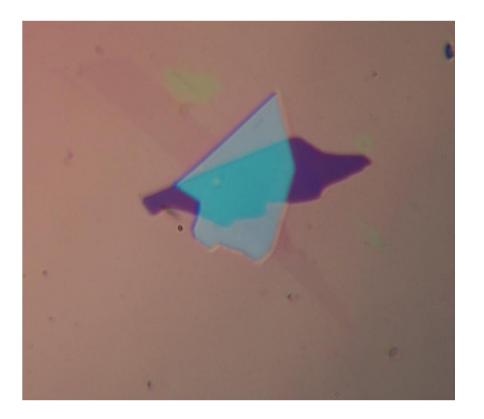




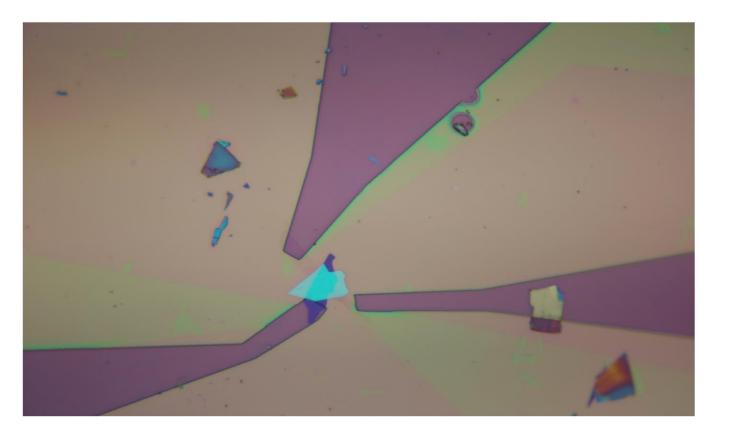


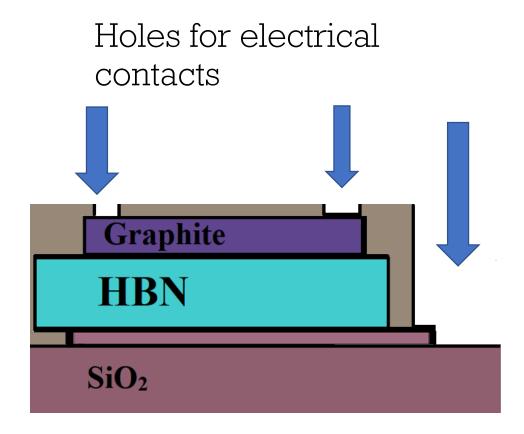
Spin Polymer for Electron Beam Lithography



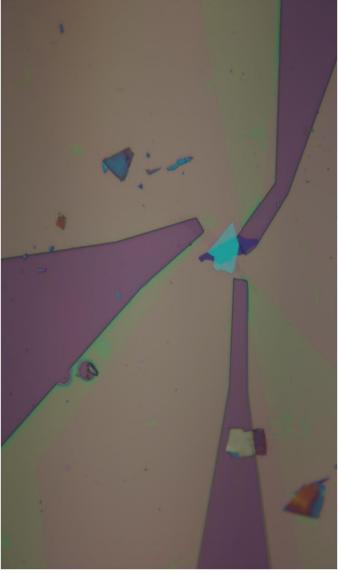


PMMA Cut from Structure

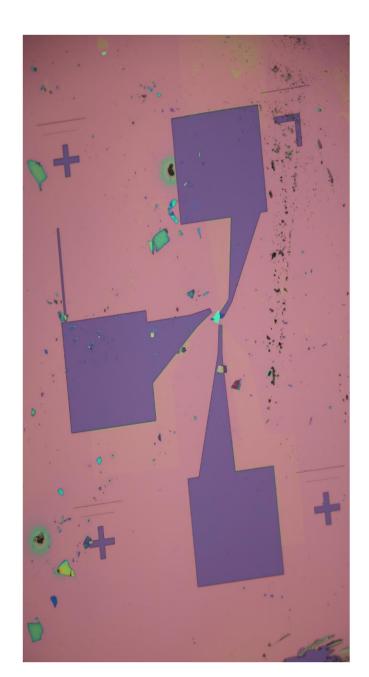




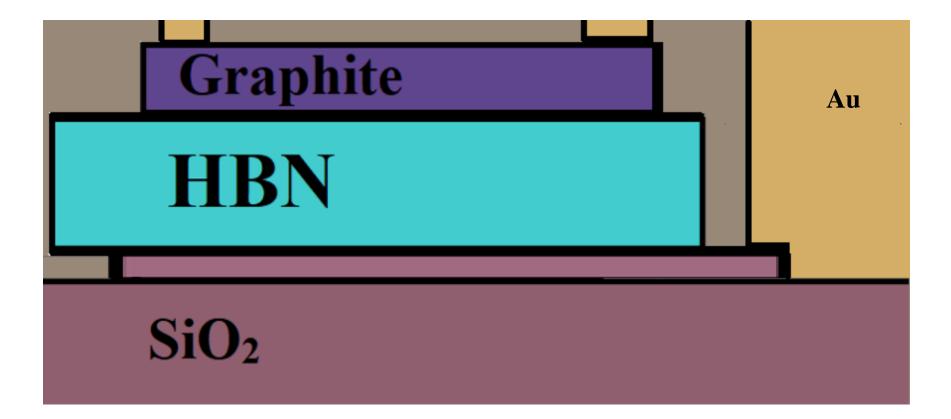
Result of EBL



Creates holes in the polymer to evaporate gold onto

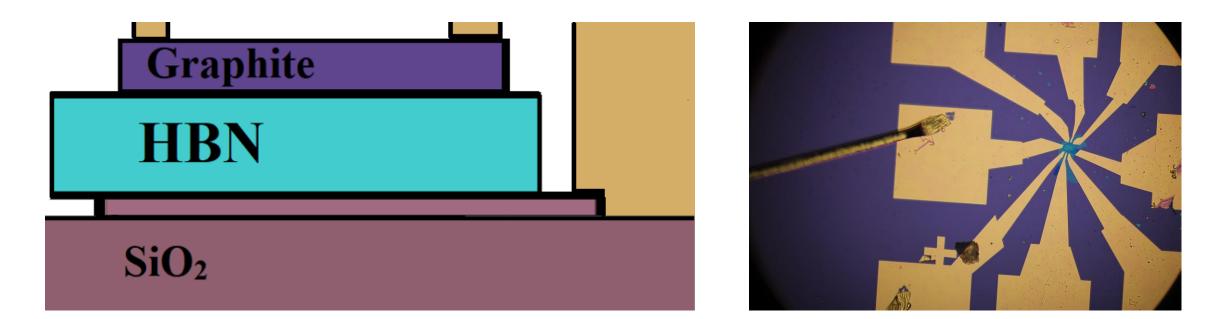


Evaporation

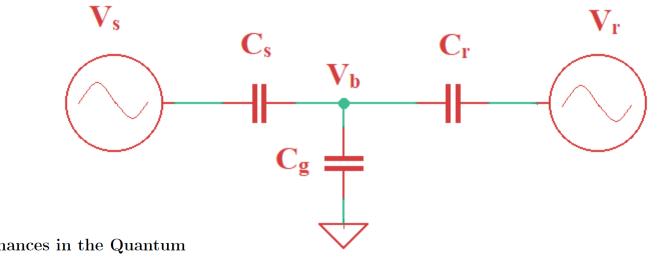


Wire Bonding

After evaporating the metal onto the device the polymer is cleaned off then the contacts are wire bonded for use



Capacitance Bridge



Imaging Transport Resonances in the Quantum

by

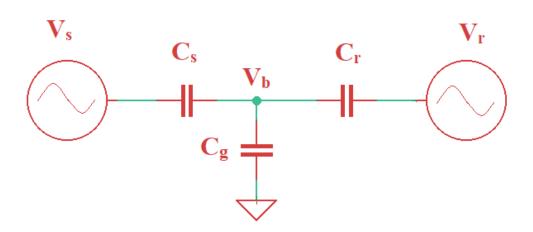
Gary Alexander Steele

Thesis, 2006

Hall Effect

Equations of Capacitance Bridge

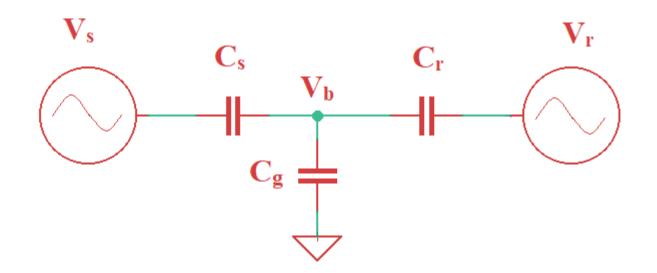
- $$\begin{split} &C_{s}V_{s}+C_{r}V_{r}=C_{T}V_{b}\\ &C_{T}=C_{s}+C_{r}+C_{g} \end{split}$$
- C_r –Ref. Capacitance
- C_r-Dev. Capacitance
- C_g Stray Capacitance to Ground

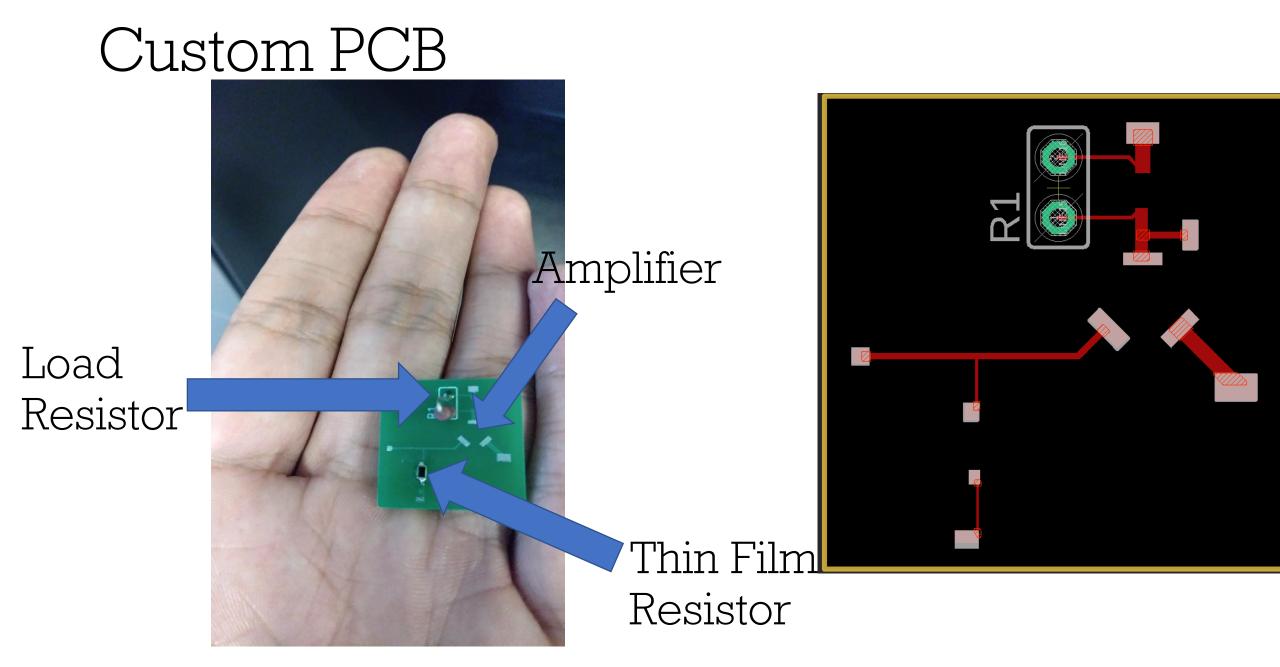


Equations of Capacitance Bridge

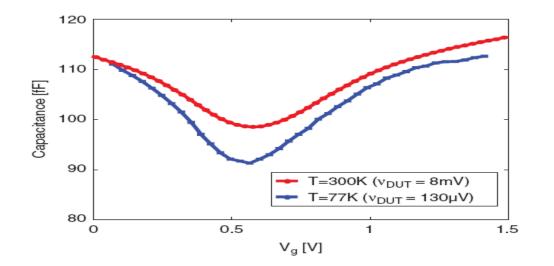
$$V_r$$
 is tuned so $V_b = 0$

 $C_s V_s = C_r V_r$





Expected Results/More work



Assembling this will create higher resolution measurements

REVIEW OF SCIENTIFIC INSTRUMENTS 82, 053904 (2011)

An integrated capacitance bridge for high-resolution, wide temperature range quantum capacitance measurements

(R=500MΩ)

Arash Hazeghi, 1, a) Joseph A. Sulpizio, 2, a) Georgi Diankov, 3 David Goldhaber-Gordon, 1, b) and H. S. Philip Wong² Department of Physics, Stanford University, 476 Lomita Mall, Stanford, California 94305, USA ²Department of Electrical Engineering, Stanford University, 476 Lomita Mall, Stanford, California 94305, USA ³Department of Chemistry, Stanford University, 476 Lomita Mall, Stanford, California 94305, USA (Received 27 September 2010; accepted 14 March 2011; published online 20 May 2011) VRF Amplifier Z_{REF} V_{b} DC HEMT gate bias CDUT **HEMT Amplifier** VDUT DUT DC sweep Reference Impedance

Conclusion

- Project can lead to better characterization of materials in the lab
- Proof of Concept

Acknowledgements

- David Cobden, Tauno Palomaki, Elliot Runburg, Paul Nguyen, Bosong Sun, Wenjin Zhao, Joshua Kahn, Zhaiyao Fei,
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